

TRENCH DMOS POWER TRANSISTOR WITH
FIELD-SHAPING BODY PROFILE AND
THREE-DIMENSIONAL GEOMETRY

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ABSTRACT

Power MOSFET apparatus, and method for its production, that suppresses voltage breakdown near the gate, using a polygon-shaped trench in which the gate is positioned, using a shaped deep body junction that partly lies below the trench bottom, and using special procedures for growth of gate oxide at various trench corners.

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